Product data sheet

1. Product profile

1.1. General description

PNP medium power transistors in a medium power SOT223 (SC73) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package	NPN comlement	
	Nexperia	JEDEC	
BCP53T	SOT223	SC-73	BCP56T
BCP53-10T			BCP56-10T
BCP53-16T			BCP56-16T

1.2. Features and benefits

- High collector current capability I_C and I_{CM}
- · Three current gain selections
- · High power dissipation capability
- · AEC-Q101 qualified

1.3. Applications

- · Linear voltage regulators
- MOSFET drivers
- · High-side switches
- · Power management
- Amplifiers

1.4. Quick reference data

Table 2. Quick reference data

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-80	V
I _C	collector current		-	-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-2	Α



80 V, 1 A PNP medium power transistors

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
h _{FE}	DC current gain						
	BCP53T	V _{CE} = -2 V; I _C = -150 mA	[1]	63	-	250	
	BCP53-10T		[1]	63	-	160	
	BCP53-16T		[1]	100	-	250	

[1] pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02$

2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		B—
3	Е	emitter		
4	С	collector	□1 □2 □3	Ë sym132

3. Ordering information

Table 4. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BCP53T	SC-73	plastic, surface-mounted package with increased heatsink;	SOT223				
BCP53-10T		4 leads					
BCP53-16T							

4. Marking

Table 5. Marking

Table of marking					
Type number	Marking code				
BCP53T	BCP53T				
BCP53-10T	P5310T				
BCP53-16T	P5316T				

80 V, 1 A PNP medium power transistors

5. Limiting values

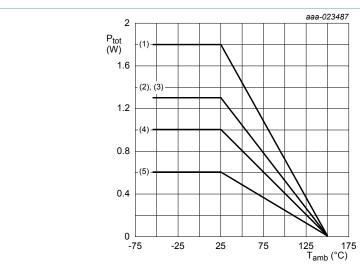
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	open emitter		-100	V
V_{CEO}	collector-emitter voltage	open base		-	-80	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-2	Α
I _B	base current			-	-0.2	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-0.3	Α
P _{tot} total power dis	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1	W
			[3]	-	1.3	W
			[4]	-	1.3	W
			[5]	-	1.8	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint.
- [5] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm.²



- (1) FR4 PCB; 4-layer copper; 1 cm²
- (2) FR4 PCB; single-sided copper; 6 cm²
- (3) FR4 PCB; 4-layer copper; standard footprint
- (4) FR4 PCB; single-sided copper; 1 cm²
- (5) FR4 PCB; single-sided copper; standard footprint

Fig. 1. Power derating curves

80 V, 1 A PNP medium power transistors

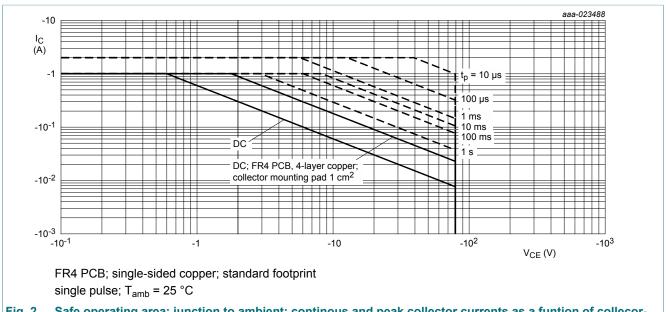


Fig. 2. Safe operating area; junction to ambient; continous and peak collector currents as a funtion of collecoremitter voltage

80 V, 1 A PNP medium power transistors

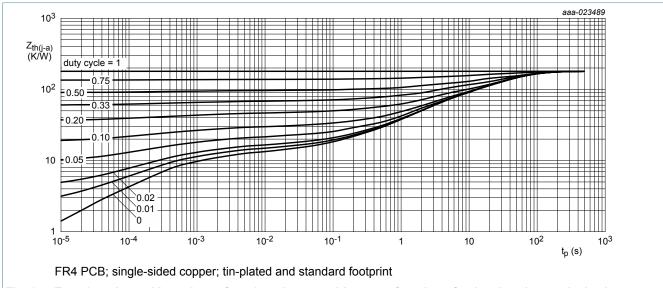
6. Thermal characteristics

Table 7. Thermal characteristics

 T_{amb} = 25 °C unless otherwise specified.

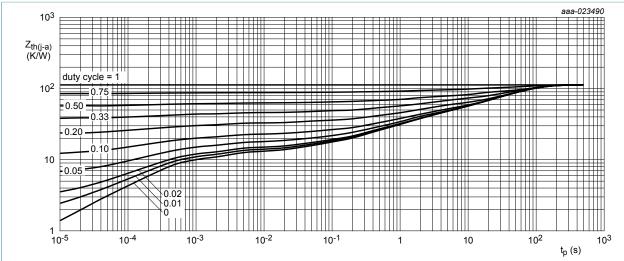
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} the	thermal resistance from junction to ambient	in free air	[1]	-	-	209	K/W
			[2]			125	K/W
			[3]			97	K/W
			[4]	-	-	97	K/W
			[5]	-	-	70	K/W
R _(j-sp)	thermal resistance from junction to solder point			-	-	18	K/W

- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm². Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 6 cm². [3]
- Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint. [4]
- [5] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm².



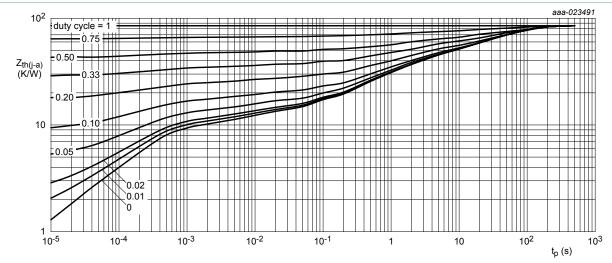
Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

80 V, 1 A PNP medium power transistors



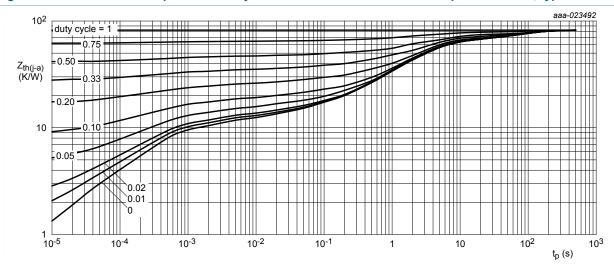
FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm²

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 6 cm²

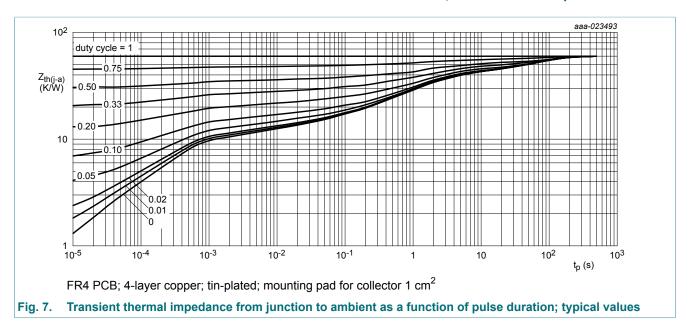
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin-plated and standard footprint

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

80 V, 1 A PNP medium power transistors



7. Characteristics

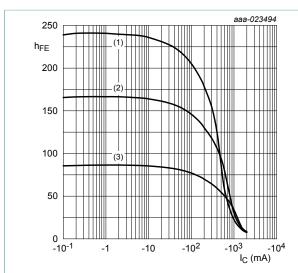
Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A$		-100	-		V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I _C = -2 mA; I _E = 0 A		-80	-		V
V _{(BR)EBO}	emitter-base breakdown voltage	I _E = -100 μA; I _C = 0 A		-5	-		V
I _{CBO}	collector-base	V _{CB} = -30 V; I _E = 0 A		-	-	-100	nA
	cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$		-	-	-10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A		-	-	-100	nA
h _{FE}	DC current gain				'		
BCP53T, -10T, -16	BCP53T, -10T, -16T	V _{CE} = -2 V; I _C = -5 mA		63	-	-	
		V _{CE} = -2 V; I _C = -500 mA	[1]	40	-	-	
	BCP53T	V _{CE} = -2 V; I _C = -150 mA	[1]	63	-	250	
	BCP53-10T	V _{CE} = -2 V; I _C = -150 mA	[1]	63	-	160	
	BCP53-16T	V _{CE} = -2 V; I _C = -150 mA	[1]	100	-	250	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	[1]	-	-	-500	mV
V_{BE}	base-emitter voltage	V _{CE} = -2 V; I _C = -500 mA	[1]	-	-	-1	V
f _T	transition frequency	V _{CE} = -5 V; I _C = -50 mA; f = 100 MHz		100	140	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	7	-	pF

[1] pulsed; $t_0 \le 300 \ \mu s$; $\delta \le 0.02$

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$$V_{CE}$$
 = -2 V

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. DC current gain as a function of collector current; typical values

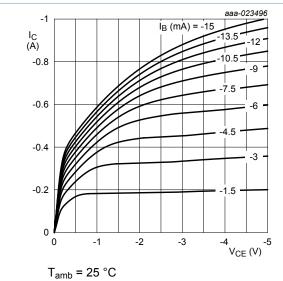
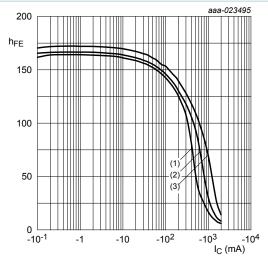


Fig. 10. Collector current as a function of collectoremitter voltage; typical values

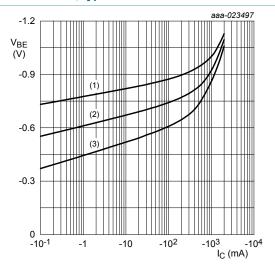


(1)
$$V_{CE} = -1 V$$

(2)
$$V_{CE} = -2 V$$

(3)
$$V_{CE} = -5 V$$

Fig. 9. DC current gain as a function of collector current; typical values



$$V_{CE}$$
 = -2 V

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

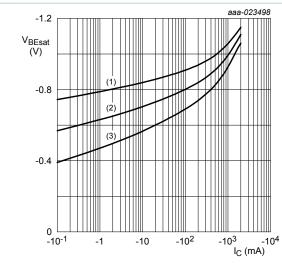
(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 11. Base-emitter voltage as a function of collector current; typical values

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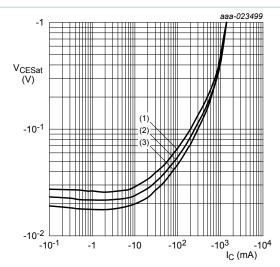
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. Base-emitter saturation voltage as a function of Fig. 13. Collector-emitter saturation voltage as a collector current; typical values



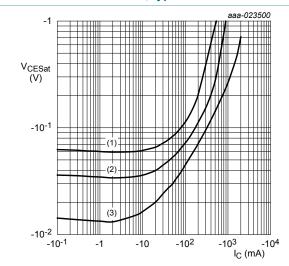
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

function of collector current; typical values



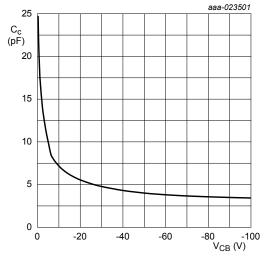
 T_{amb} = 25 °C

(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3) $I_C/I_B = 5$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

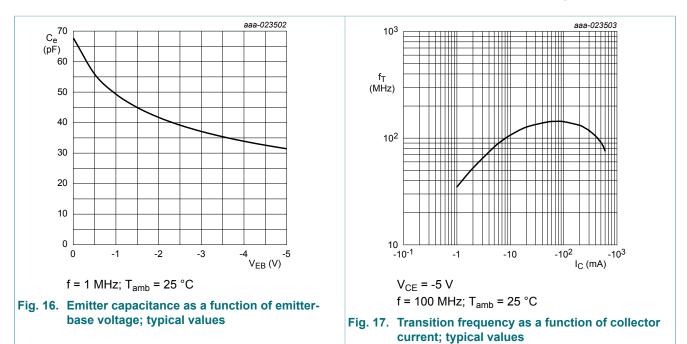


 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig. 15. Collector capacitance as a function of collectorbase voltage; typical values

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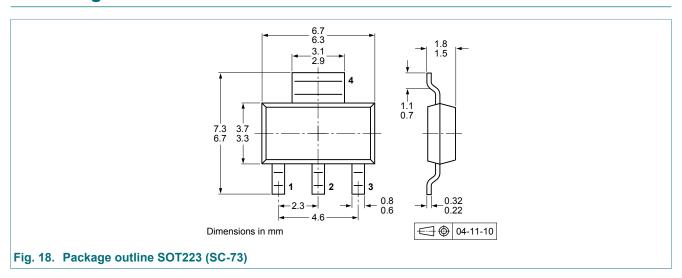


8. Test information

8.1. Quality information

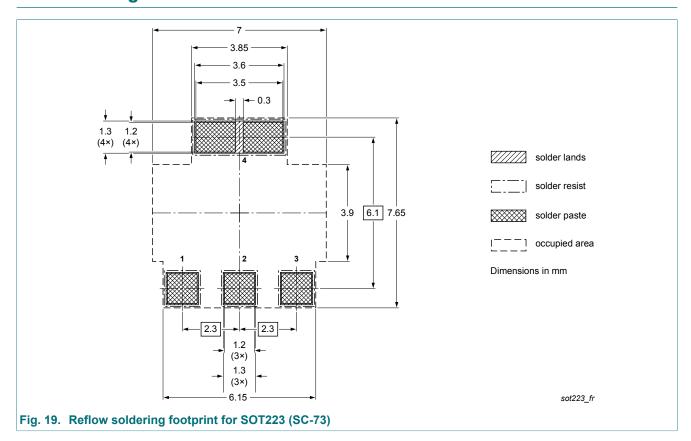
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

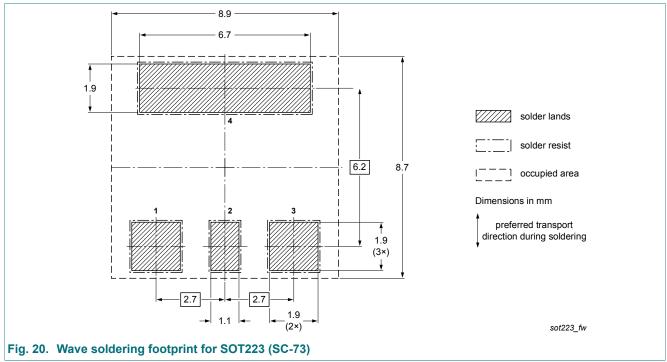
9. Package outline



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10. Soldering





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11. Revision history

Table 9. Revision history

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Document ID	Release date	Data sheet status	Change notice	Supersedes		
BCP53T_SER v.2	20190429	Product data sheet	-	BCP53T_SER v.1		
Modifications:	The format of the of Nexperia.	acteristics: breakdown voltages added ormat of this data sheet has been redesigned to comply with the identity guideline xperia. I texts have been adapted to the new company name where appropriate.				
BCP53T_SER v.1	20160705	Product data sheet	-	-		

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Nexperia

BCP53T series

80 V, 1 A PNP medium power transistors

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 29 April 2019

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